# NSN 5961-00-103-1639

Transistor - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-00-103-1639

Inclosure Material:

Metal

**Overall Length:** 

0.372 inches

## **Overall Diameter:**

0.347 inches

# **Mounting Facility Quantity:**

1

## Internal Configuration:

Junction contact

# Electrode Internally-electrically Connected To Case:

Base

#### **Mounting Method:**

Threaded stud

#### Features Provided:

#### Hermetically sealed case

#### **Overall Width Across Flats:**

0.432 inches

# Thread Size:

0.190 inches

## Semiconductor Material:

Silicon

# Voltage Rating In Volts Per Characteristic:

100.0 breakdown voltage, collector-to-base, emitter open and 8.0 breakdown voltage, emitter-to-base, collector open

# **Current Rating Per Characteristic:**

Between 1.00 amperes source cutoff current and 10.00 amperes source cutoff current

# Power Rating Per Characteristic:

40.0 watts small-signal input power, common-collector

# Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

#### **Special Features:**

Junction pattern arrangement: npn

#### **Thread Series Designator:**

Unf

#### **Terminal Type And Quantity:**

1 threaded stud and 3 tab, solder lug

Shelf Life:

N/a

#### Unit Of Measure:

--

#### Demilitarization:

No

# **NSN 5961-00-103-1639** Transistor - Page 2 of 2

Fiig: A110a0

